

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF THE CLAIMS

Claims 1-29 (Cancelled)

Claim 30 (Currently amended) A field effect transistor comprising:

a substrate of a single crystal semiconducting material,
two spaced apart metal semiconductor compound regions forming a source and
drain and defining a channel there between,
a first dielectric layer on said source and drain adjacent said channel,
a gate dielectric layer of locally reacted metal of said metal used in said metal-
semiconductor compound regions on said channel, and
a conductive layer on said ~~gate dielectric~~ gate dielectric layer to form a gate.

Claims 31-32 (Cancelled)

Claim 33 (Original) The field effect transistor of claim 30 wherein said gate dielectric layer
includes TiO_2 .

Claims 34-64 (Cancelled)

Claim 65 (Newly added) The field effect transistor of claim 30 wherein said two spaced apart
metal semiconductor compound regions further include an additional layer of conductive

material between said metal and said first dielectric layer, said additional layer of conductive material having sidewalls, said sidewalls having insulating material disposed thereon.

Claim 66. (Newly added) The field effect transistor of claim 65 wherein said additional layer of conductive material includes an oxidizable material.

Claim 67. (Newly added) The field effect transistor of claim 65 wherein said additional layer of conductive material is selected from the group consisting of Al, Co, Er, Ni, Pd, Pt, Rh, Ta, Ti and W.

Claim 68. (Newly added) The field effect transistor of claim 65 wherein said metal of said metal semiconductor compound regions is selected from the group consisting of Al, Co, Er, Ni, Pd, Pt, Rh, Ta, Ti, and W.

Claim 69. (Newly added) The field effect transistor of claim 65 wherein said two spacer apart metal semiconductor compound regions include Ta and said additional layer of conductive material includes Al.

Claim 70. (Newly added) The field effect transistor of claim 65 wherein said insulating material disposed on said sidewalls of said additional layer of conductive material also covers sidewalls of said first dielectric layer.

Claim 71. (Newly added) The field effect transistor of claim 65 wherein said insulating material disposed on said sidewalls of said additional layer of conductive material includes an oxide of said additional conductive material.